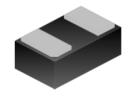


# **Bi-directional 3.3V Normal Capacitance ESD Protector**

### **Description**

The PESDNC2FD3V3B protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one bi-directional line in applications where arrays are not practical.



DFN1006-2L(Bottom View)

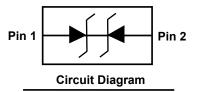
### **Feature**

- $\rightarrow$  45W peak pulse power per line ( $t_P = 8/20\mu s$ )
- DFN1006-2L package
- Replacement for MLV(0402)
- Bidirectional configurations
- > Response time is typically < 1ns
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to IEC61000-4-2(ESD) ±30KV(air), ±30KV(contact); IEC61000-4-4 (EFT) 40A (5/50ns)

### **Applications**

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

Rev 06 6





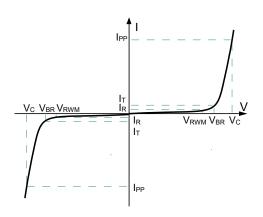
www.prisemi.com

#### **Mechanical Characteristics**

- Mounting position: Any
- Qualified max reflow temperature:260°C
- Device meets MSL1 requirements
- DFN1006-2L without plating

## **Electronics Parameter**

Symbol	Parameter		
$V_{RWM}$	Peak Reverse Working Voltage		
I <sub>R</sub>	Reverse Leakage Current @ V <sub>RWM</sub>		
$V_{BR}$	Breakdown Voltage @ I⊤		
lτ	Test Current		
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ I <sub>PP</sub>		
P <sub>PP</sub>	Peak Pulse Power		
CJ	Junction Capacitance		
IF	Forward Current		
VF	Forward Voltage @ I <sub>F</sub>		



# Electrical characteristics per line@25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Stand-off Voltage	V <sub>RWM</sub>				3.3	V
Reverse Breakdown Voltage	V <sub>BR</sub>	I <sub>t</sub> = 1mA	4.5			V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 3.3V T=25°C			1.0	μA
Clamping Voltage	V <sub>CL</sub>	I <sub>PP</sub> =16A t <sub>p</sub> =100ns		10		V
Clamping Voltage	Vc	I <sub>PP</sub> =5A		8.5	10.5	V
Junction Capacitance	Cj	V <sub>R</sub> =0V f = 1MHz		12		pF

## Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Unidirectional Peak Pulse Power	P <sub>pp</sub>	45	W
Peak Pulse Current (t <sub>p</sub> =8/20μs)	I <sub>pp</sub>	6	Α
Operating Temperature	Тл	-55 to 150	°C
Storage Temperature	T <sub>STG</sub>	-55 to 150	°C

## **Typical Characteristics**

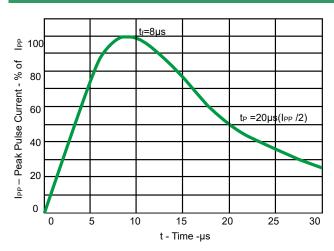
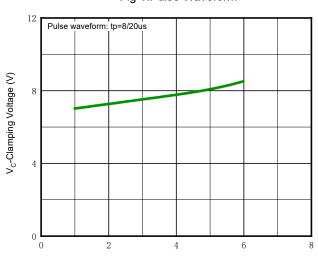


Fig 1.Pulse Waveform



I<sub>PP</sub>-Peak pulse current (A) Fig 3. Clamping voltage vs. Peak pulse current

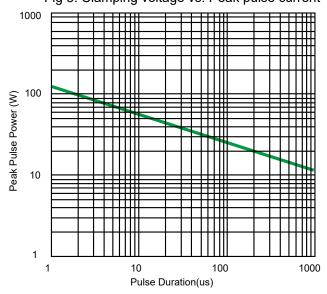


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

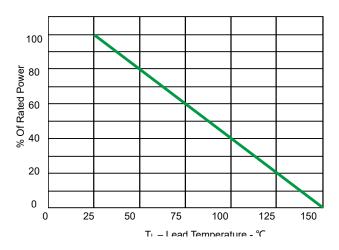
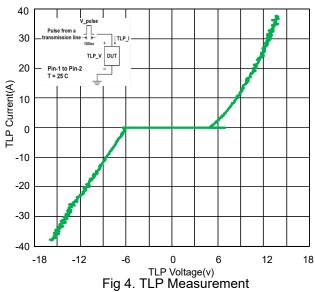
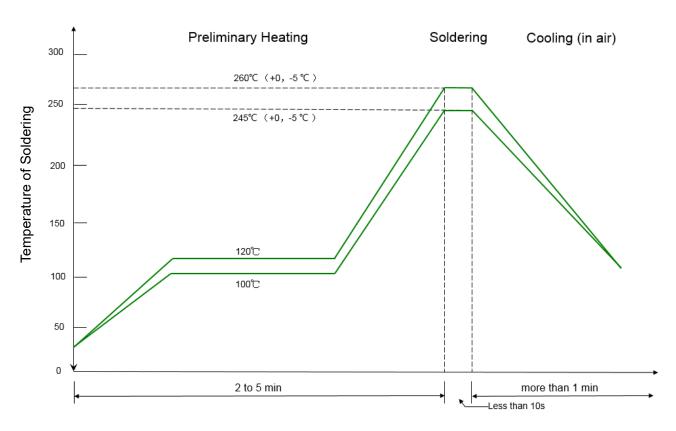


Fig 2.Power Derating Curve



### **Solder Reflow Recommendation**



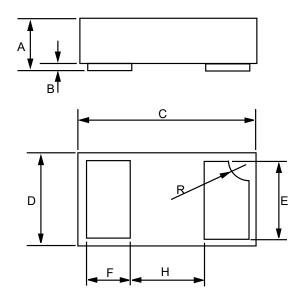
Remark: Pb free for 260°C; Pb for 245°C

### **PCB** Design

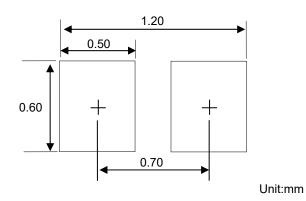
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.

# Product dimension (DFN1006-2L)



Dim	Inches		Millimeters		
	MIN	MAX	MIN	MAX	
Α	0.013	0.020	0.34	0.498	
В	0.000	0.002	0.00	0.05	
С	0.037	0.043	0.95	1.080	
D	0.022	0.027	0.55	0.680	
E	0.016	0.024	0.40	0.60	
F	0.008	0.012	0.20	0.30	
Н	0.015Typ.		0.40Тур.		
R	0.001	0.005	0.05	0.15	



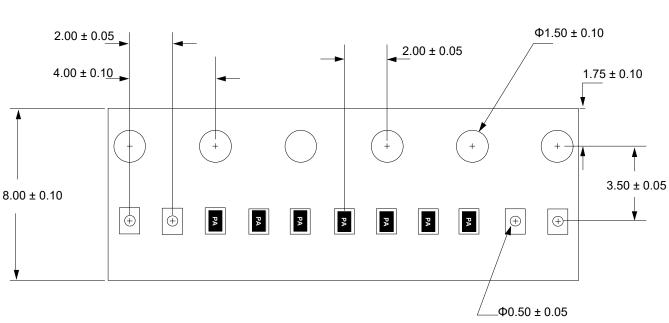
Suggested PCB Layout

# Ordering information

Device	Package	Reel	Shipping
PESDNC2FD3V3B	DFN1006-2L (Pb-Free)	7"	10000 / Tape & Reel

## **Load with information**





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